

140 COMMERCE DRIVE MONTGOMERYVILLE, PA 18936-1013

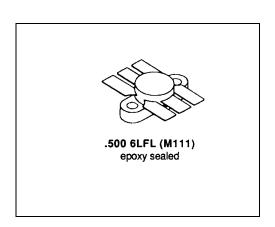
PHONE: (215) 631-9840 FAX: (215) 631-9855

MS1003

RF & MICROWAVE TRANSISTORS VHF MOBILE APPLICATIONS

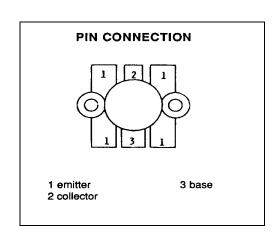
Features

- 175 MHz
- 12.5 VOLTS
- P_{OUT} = 100 WATTS
- G_P = 6.0 dB MINIMUM
- COMMON EMITTER CONFIGURATION



DESCRIPTION:

The MS1003 is a 12.5 V Class C epitaxial silicon NPN transistor designed primarily for VHF, FM communications. Diffused emitter resistors provide high VSWR capability under rated operating conditions. Internal impedance matching ensures optimum power gain and efficiency over the 136-175 MHz band.



ABSOLUTE MAXIMUM RATINGS (Tcase = 25° C)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	36	V
V _{CEO}	Collector-Emitter Voltage	18	V
V _{CES}	Collector-Emitter Voltage	36	V
V_{EBO}	Emitter-Base Voltage	4.0	V
Ic	Device Current	20	Α
P _{DISS}	Power Dissipation	270	W
TJ	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Thermal Data

R _{TH(J-C)}	Junction-case Thermal Resistance	0.65	°C/W



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ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

STATIC

Symbol	Test Conditions			Value		
Syllibol			Min.	Typ.	Max.	Unit
BV _{CBO}	$I_C = 50mA$	I _E = 0mA	36			V
BV _{CES}	I _C = 100mA	$V_{BE} = 0V$	36			V
BV _{CEO}	I _C = 100mA	$I_B = 0mA$	18			V
BV _{EBO}	I _E = 10mA	$I_C = 0mA$	4.0			٧
I _{CES}	V _{CE} = 15V	I _E = 0mA			15	mA
h _{FE}	$V_{CE} = 5V$	I _C = 5A	10		100	

DYNAMIC

Symbol Test Conditions		Value		Unit			
Symbol	rest conditions		Min.	Typ.	Max.	Offic	
P _{out}	f =175 MHz	$P_{IN} = 25 W$	$V_{CC}=12.5V$	100			W
G _P	f =175 MHz	P _{IN} = 25 W	V _{CC} =12.5V	6.0			dB
Сов	f = 1 MHz	$V_{CB} = 12.5 \text{ V}$				390	pF

IMPEDANCE DATA

FREQ	$Z_IN(\Omega)$	$Z_{CL}(\Omega)$
175 MHz	1.5 - j0.9	0.5 - j1.0



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PACKAGE MECHANI CAL DATA

